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SUPPORTING INFORMATION

Experimental characterization of defects in copper antimony disulfide

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Fig. S1 XRD patterns for crystals-film, and pre-TT and TT-11h films. The standard XRD pattern used as comparison (vertical green lines) was the ICSD-85133 orthorhombic CuSbS₂.



Fig. S2 Excitation power dependence of the derived PL spectra for A) peak 3 on the crystalsfilm and B) peak 1+2 on TT-11h film.



Fig. S3 Scanning electron microscope (SEM) images were taken in FEI Quanta 600 instrument. Surface and cross-section images of the A) pre-TT, B) TT-11h (3.5 μ m scale / 2 μ m scale) films and C) crystals-film (24 μ m scale / 1 μ m scale), respectively.



Fig. S4 Temperature dependence of the PL spectra for TT-11h film A) from 4.25 to 53 K and B) from 50 to 298 K (normalized PL counts scale).